

FIRST PRINCIPLE STUDY OF STRUCTURAL, ELECTRONIC, ELASTIC AND OPTICAL PROPERTIES OF TiXF_3 (X = AG AND PD) EMPLOYING ACCURATE TB-MBJ APPROACH

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ABSTRACT: This research presents within the full potential linearized augmented plane wave (FP-LAPW) technique with the first-principles calculations to investigate the structural, electronic, elastic and optical properties of ternary cubic perovskites of the form TiXF_3 (X= Ag and Pd) compounds. All these calculation is done by WIEN2k code within the density functional theory (DFT). The modified Becke–Johnson potential (TB-mBJ) is used for the optical and electronic properties. TDOS and PDOS analysis shows that both TiAgF_3 and TiPdF_3 are structurally stable and the main contribution of the states in TiAgF_3 compound is due to the Ti (d-orbitals) atoms and that in TiPdF_3 compound, F (p-states) contributes the more. The electronic-band structure analysis shows the metallic properties having no band gaps. Optical properties are also discussed using dielectric function. Elastic calculation revealed that both compounds are anisotropic, brittle and ionic.

Keywords: Density Functional Theory, Electronic property, Density of state, Optical property, Band structure, Elastic property.

1. INTRODUCTION

Any material have a nearly cubic crystal structure is called a Perovskite. The general chemical formula for perquisite compounds is ABX_3 , where ‘A’, ‘B’ shows ions of different sizes, and X is an ion (frequently oxide) or fluorides that bonds to both ions. The ‘A’ atoms are generally larger than the atoms ‘B’ due to coordination number. Coordination number of A is 12 while the coordination number of B is 6. We will investigate the optical and electronic properties of both compounds in order to know their best use. Perovskites are used in various fields due to their wide range of electrical, optical, insulating and semiconducting behavior. Perovskites are found in the inner part of earth. Perovskite is being acknowledged among different materials with broad application in science and technology. It is used in electronic equipment’s, renewable energy resources, and defense system due to their high photoelectric properties. The electrical resistance of perovskites changes when they are placed in

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the magnetic field. Perovskites compounds have same crystal structure as those of minerals and ceramics. Perovskite was discovered by Gustav Rose and was given the name “perovskite” in recognition of the important research work of Lev Perovski. Calcium titanate ($CaTiO_3$) is the chemical formula for natural occurring perovskite mineral [1]. Because of low refractive index, this fluoride-type material can be used for defense system, anti-reflection coating and in optics. The theoretical analysis of the structural and electronic properties of fluoride type prerequisites $TiAgF_3$ and $TiPdF_3$ are calculated. The modified Becke–Johnson potential (TB-mBJ) and exchange correlation is used within WIEN2k code [2] for application.

2. COMPUTATIONAL AND STRUCTURAL AND DETAIL

The structures for both the cubic fluoro Perovskites $TiAgF_3$ and $TiPdF_3$ having space group $Pm-3m$ (#221) are shown in Figure 1. $TiAgF_3$ unit cell is occupied with Wyckoff positions: $Ti = (0,0,0)$, $Ag = (1/2, 1/2, 1/2)$ and $F = (0, 1/2, 1/2)$. Similarly, for $TiPdF_3$ the occupied Wyckoff positions are $Ti = (0 0 0)$, $Pd = (1/2,1/2 1/2)$ and $F = (0, 1/2,1/2)$. The number of k-points used in the Brillouin zone are 1,000. The potential wave and charge density are explained in the form of Fourier series vectors up to $G_{max} = 12 \text{ au}^{-1}$ [3].

In both structures, Ti, Ag and Pd change their sites. Lattice constant $a = 4.52 \text{ \AA}$ have been used for computation. The full potential linearized augmented plane wave (FP-LAPW) method of Kohn and Sham-density functional theory, is introduced in “WIEN2K code” to investigate the electronic structures [4]. The cut-off factor is:

$$R_{MT} \times K_{max} = 7$$

in which K_{max} shows the highest value of reciprocal lattice vector in the plane wave expansion, “ R_{MT} ” shows the lowest atomic sphere radius. The standard total energy calculation for the convergence of the self-consistent in density functional theory is 0.0001 Ry.

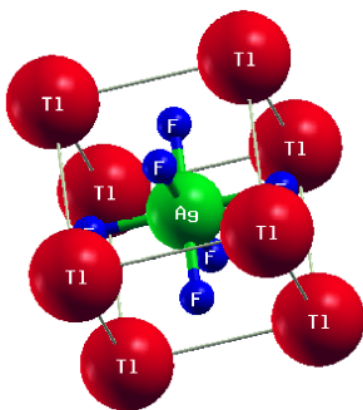


Figure 1. Crystal structure of $TiXF_3$ perovskite (X= Ag and Pd).

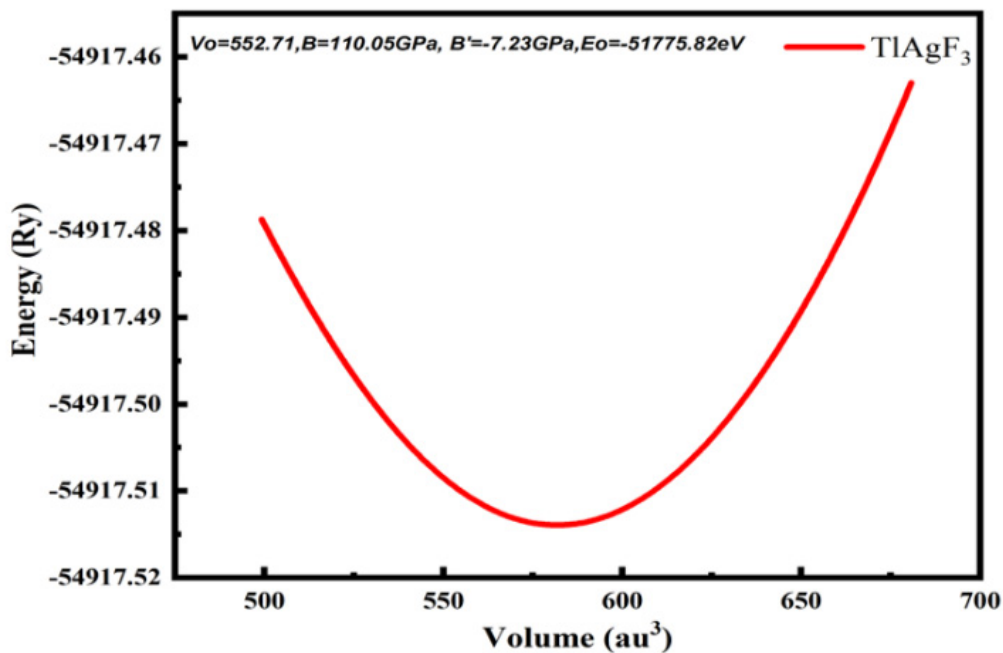
3. RESULTS AND DISCUSSIONS

3.1 VOLUME OPTIMIZATION

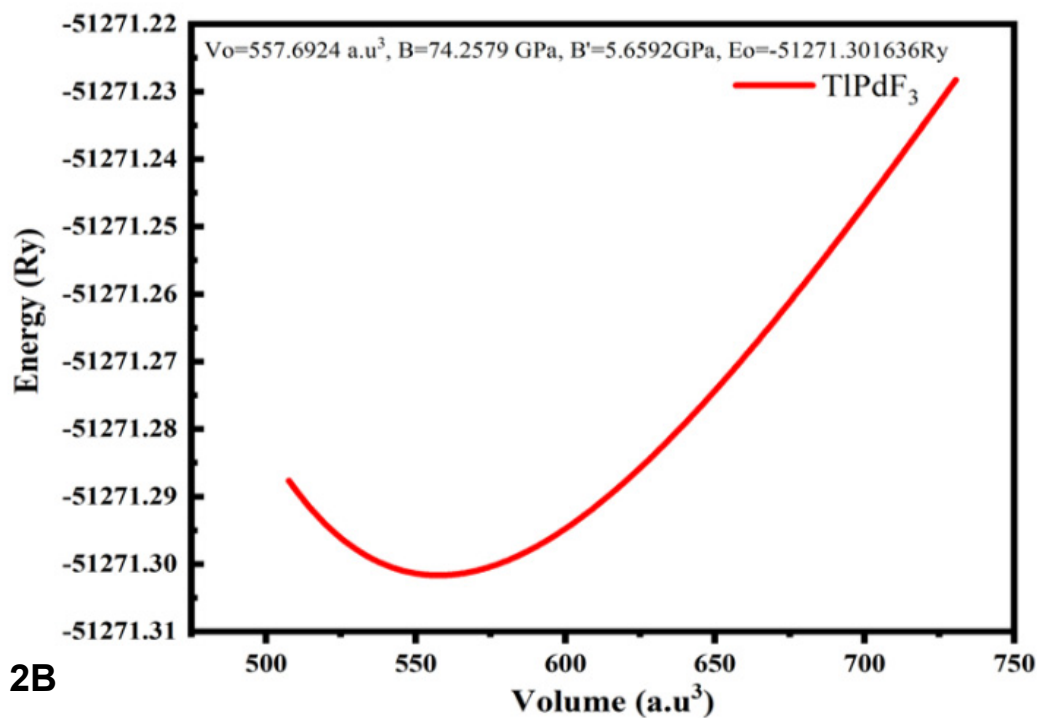
The structural optimization of $TiAgF_3$ and $TiPdF_3$ is calculated through Murnaghan's equation of state [5] to get equilibrium lattice constants. Volume optimization is the relaxed structure with minimum energy. Experimental values of the lattice parameters are slightly less than the observed values as shown in Figures 2A and 2B. The structural optimization defines the obtained energy versus volume plot for $TiAgF_3$ and $TiPdF_3$ are given in the Table 1. The equilibrium lattice constants (a), bulk modulus "B" and its pressure derivatives (B') are shown in Figures 2A and 2B. As the volume decreases, the initial energy of the unit cell increases. The lowest energy state (E_0) is acquired at a certain points where the energies of the system is minimum. Thus it is concluded that both the compounds are structurally stable at this point. This minimum volume corresponding to lowest energy level is known as optimized volume or ground state. Once ground state energy level is obtained, the system once again becomes unstable by increasing the unit cell volume. These investigation revealed for the first time and well matched with the given values in (AFLOW) literature [6]. Bulk modulus (B_0) shows the stiffness of the materials, which is greater for $TiAgF_3$ as compared for $TiPdF_3$. Therefore the $TiAgF_3$ is more soft and ductile as compared to $TiPdF_3$. It is also investigated that the energy needed to form $TiAgF_3$ structure is greater than that for $TiPdF_3$. The strength of the materials represent by bulk modulus "B" while pressure derivatives (B') is necessary to know thermoplastic properties of a material [7].

Table 1 Structural parameters i.e pressure derivatives 'B' lattice constants 'a₀', and its bulk modulus 'B₀' at zero pressure.

Compound	Lattice constants a "Å"	Bulk modulus B ₀ in (GPa)	Pressure Derivatives "B."	Ground states energies "E ₀ "	Ground state Volume (v ₀)
TiAgF ₃	4.43	110.05	7.23	-51775.82	552.71
TiPdF ₃	4.43	74.2579	5.6592	-51271.30	557.6924



2A



2B

Figures 2A and 2B. Volume optimization curves for $TiXF_3$ (X = Ag, Pd) cubic perovskites. 2A: $TiAgF_3$; 2B: $TiPdF_3$.

4. DENSITY OF STATES (DOS)

The density of states (DOS) illustrates the contributions of various electronic states and show an essential part to know the electronic properties of different materials. The total density of states (T-DOS) and partial density of states (P-DOS) of $TlAgF_3$ and $TlPdF_3$ compounds respectively are shown in Figures 3A and 3B.

The T-DOS plot of $TlAgF_3$ is shown in Figure 3A maximum peak in the valence band, are observed at -4.3 eV below the fermi level. Similarly two other small peaks of T-DOS plot are seen in the valence band due to F and Pd atoms at -4.3 eV and -2.1 eV respectively. In the P-DOS of $TlPdF_3$, the main contribution of F-p state electrons and less contribution of Tl-f state electrons in the conduction band above the fermi level. The total DOS peak lies at 7.0 eV and partial DOS are at 5.0 eV due to the contribution of Tl-p states electron respectively. However conduction and valence band overlaps and there is no band gap between. Hence $TlPdF_3$ are metallic in nature [8].

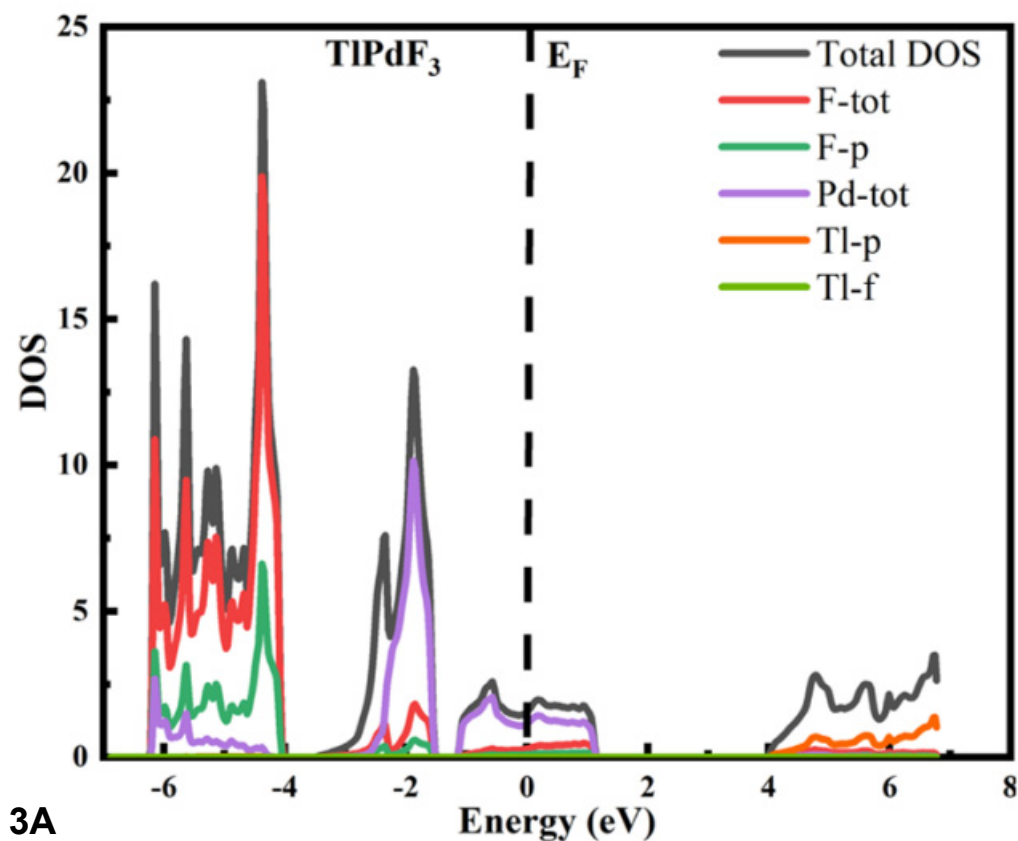


Figure 3A: T-DOS and P-DOS of $TlPdF_3$.

The total density of states (T-DOS) and partial density of states (P-DOS) plots of TlAgF_3 are shown in the Figure 3B. In the valence band, the total DOS peak of TlAgF_3 observed at -2.0 eV below the fermi level. In the case of partial density of states, the main contribution are due to Tl atoms individually which are in the valence region[9]. Two other small peaks are observed due to the contribution of p and d state electron in the valence region above the fermi level at -1.9 eV and -2.3 eV respectively. However there is no band gap between the valence and conduction band so TlAgF_3 are also metallic in nature[9].

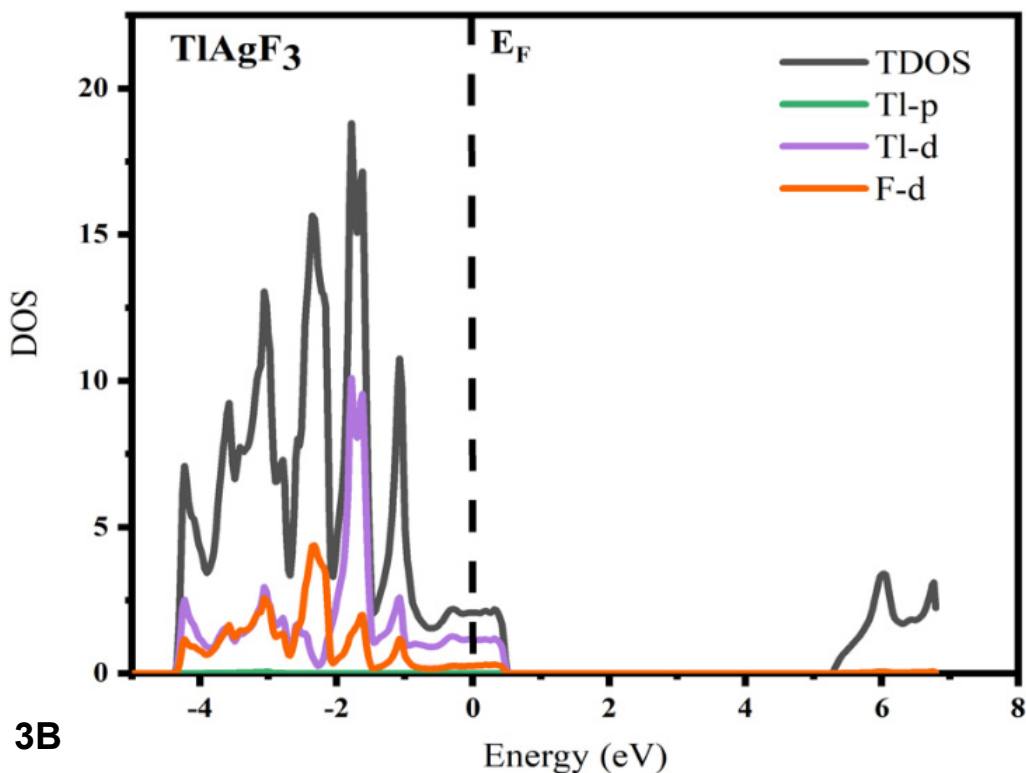


Figure 3B. T-DOS and P-DOS of TlAgF_3 .

5. BAND STRUCTURES

The calculated electronic high-symmetry directions band structure for both fluoro-perovskites TlAgF_3 and TlPdF_3 of the Brillouin zone are illustrated in Figures 4A and 4B. Investigating the electronic band structure of these compounds can give us exact information of the best application in the fields of optics and electronics. Electronic band structure gives range of energy levels of electrons and also range of forbidden energy gaps. The electronic band structures were determined using the stable lattice constants.

As shown in Figures 4A and 4B. The electronic band structures of TlAgF_3 and TlPdF_3 on the selected “ $R-\Gamma-X-M-\Gamma$ ”

(TB-mBJ) method[10]. Fermi energy level is taken at 0.0 eV. Valence band maxima and conduction band minima lies on different symmetry points. The inner state electrons of Tl, Pd and F atoms in the Conduction band, the lowest energy band lies at 2.3 eV above Fermi level. At the symmetry point R in the valence region, the maximum band energy lies at 0.9 eV. In the conduction region, minimum energy occurs at 2.7 eV, at the symmetry point Γ above the Fermi level [10]. Thus it is concluded from the graph that along R - Γ symmetry directions, an indirect transition takes place. In this case our values are smaller than the band gap acquired from experimental values (10.9 eV). The observed total DOS plot of $TlAgF_3$ is shown in Figure 4A.

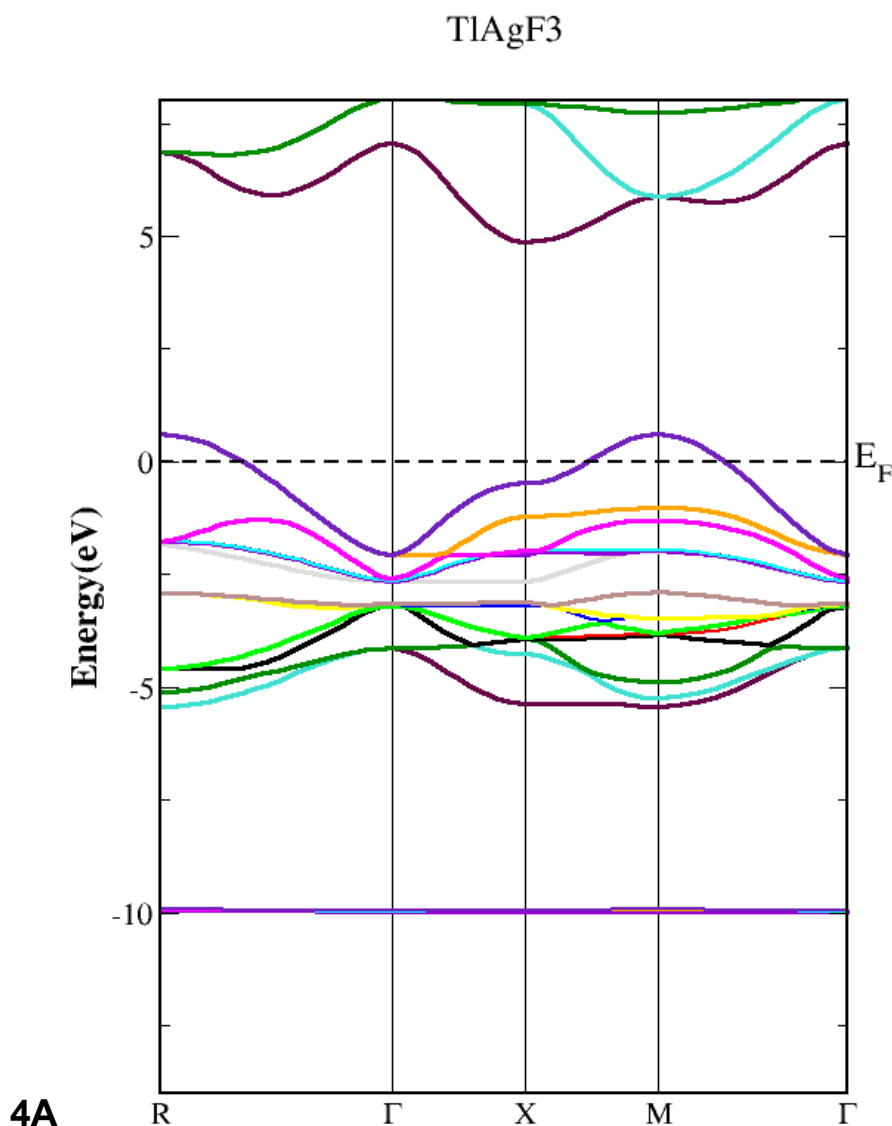


Figure 4A. Shows band structures of $TlAgF_3$.

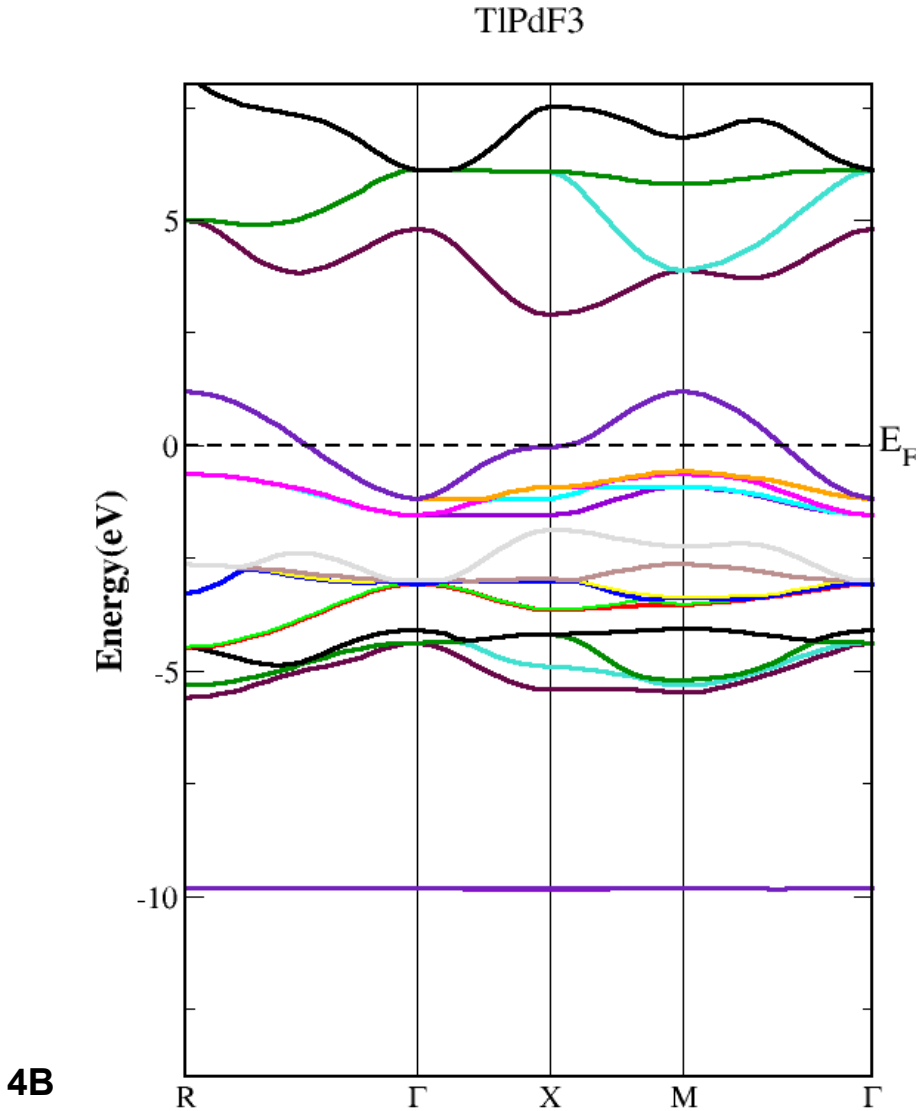


Figure 4B. Shows band structures of $TiPdF_3$.

6. OPTICAL PROPERTIES

FP-LAPW method is used to determine the optical properties of both compounds. To analyze the result of $TiAgF_3$ and $TiPdF_3$ to incident photons, refractive index $\eta(\omega)$, Optical reflectivity $R(\omega)$, optical conductivity $\sigma(\omega)$, absorption coefficient $I(\omega)$, energy loss $L(\omega)$ and electron extinction coefficient $K(\omega)$ are determined [11]. The optical properties are described by means of the complex dielectric function

$$\epsilon(\omega) = \epsilon_1(\omega) + i\epsilon_2(\omega) \quad (i)$$

where $\epsilon_1(\omega)$ and $\epsilon_2(\omega)$ represents the real and imaginary parts respectively. The dielectric function and band structure of the electronic material are closely related to

each other. The optical properties of material can be determined by dielectric function. The real component $\epsilon_1(\omega)$ shows polarizability of a material. The calculated $\epsilon_1(\omega)$ dielectric functions spectrum is shown in figure (x) and (y). The real part of the function “ $\epsilon_1(\omega)$ ” shows the electronic polarizability of a material [11]. The zero frequency limit $\epsilon_1(0)$ is obtained at zero called static dielectric constant. This zero frequency limit lies nearly at as 5.2 in Figure 5 for $TlPdF_3$ and 4.3 for $TlAgF_3$. The electronic band structure and absorptive behavior of a material is described by $\epsilon_2(\omega)$ of the dielectric function. It is the addition of all the transition between the valence band and the conduction band as shown by Figure 5. For imaginary part the threshold value of energy lying around 7.3 eV and 5.4 eV for $TlPdF_3$ and $TlAgF_3$.

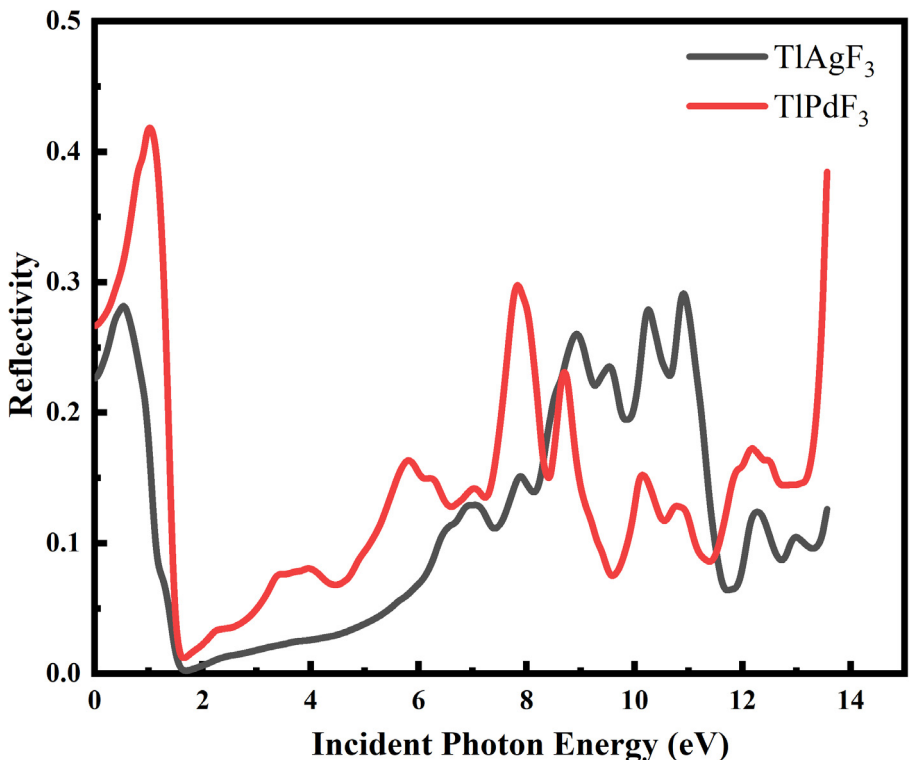


Figure 5. The calculated reflectivity $R(\omega)$ of $TlPdF_3$ and $TlAgF_3$.

6.1 THE REFLECTIVITY $R(\omega)$

The reflectivity $R(\omega)$ spectrum is formed by sharing Tl-p states electrons in the valence band while X-d states electrons in the conduction band as seen in Figure 5 for $TlPdF_3$ and $TlAgF_3$. $R(0)$ represents zero frequency reflectivity which is 10% for $TlPdF_3$ and 15% for $TlPdF_3$. The reflectivity coefficient “ $R(\omega)$ ” lies between 0.0 eV and 40eV and is smaller than 10% [12]. Reflectivity obtained at maximum value of 35% at 5.2eV for $TlPdF_3$ and 30% at 4.6eV for $TlAgF_3$ as shown in Figure 5.

6.2 THE REFRACTION

Refractive index shows an important parameter and helpful in finding photoelectric effect [13]. So it is necessary to know all about the refraction of light. Optically isotropic nature of TlPdF_3 and TlAgF_3 are observed in the lower energies range. Refractive index represents complex number consists of real and imaginary numbers. Refractive index $\eta(\omega)$ are real parts of the function while $K(\omega)$ also known for extinction coefficient imaginary part as illustrated in Figure 6. For TlPdF_3 and TlAgF_3 the static refractive index $\eta(0)$ lies at 2.8 and 3.3 respectively. For TlPdF_3 , the highest refractive index rate is 5.0 at 3.9eV and 2.2eV for TlAgF_3 .

Incident photon absorbed and slowed down by target material therefore their $\eta(\omega)$ value is greater than one [14]. Refractive index will be greater when a large number of photons slowed down due to interaction with a materials. Refractive index also depends on the type of bonding. Refractive index values in covalent bond is greater than ionic one because covalent bond share more electron than ionic [15]. Therefore due to covalent bonding maximum electrons are spread throughout the material and hence more chance for incident photon to be slowed down. The extinction coefficient $K(\omega)$ (imaginary part) are shown in Figure.6.

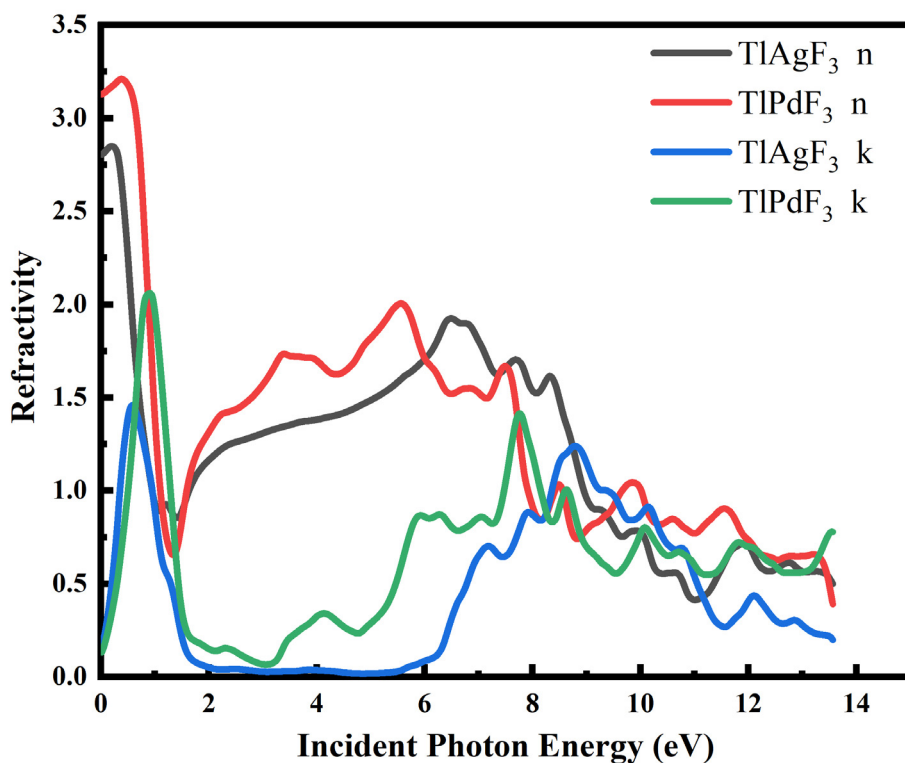


Figure 6. The refractive index $\eta(\omega)$ of TlPdF_3 and TlAgF_3 .

6.3. THE CONDUCTIVITY $\sigma(\omega)$

Optical conductivity $\sigma(\omega)$ is the electron conductivity due to applied electromagnetic field [16]. The calculated $\sigma(\omega)$ for $TlPdF_3$ and $TlAgF_3$ are shown in fig.7. The optical conductivity $\sigma(\omega)$ spectra increases sharply at a point called critical point of 35 eV for $TlPdF_3$ and at 7 eV for $TlAgF_3$. The highest optical conductivity $\sigma(\omega)$ recorded approximately to be $4300 \Omega^{-1}cm^{-1}$ at 8 eV for $TlAgF_3$ and for $TlAgF_3$ it is $3900 \Omega^{-1}cm^{-1}$ at 8.3 eV.

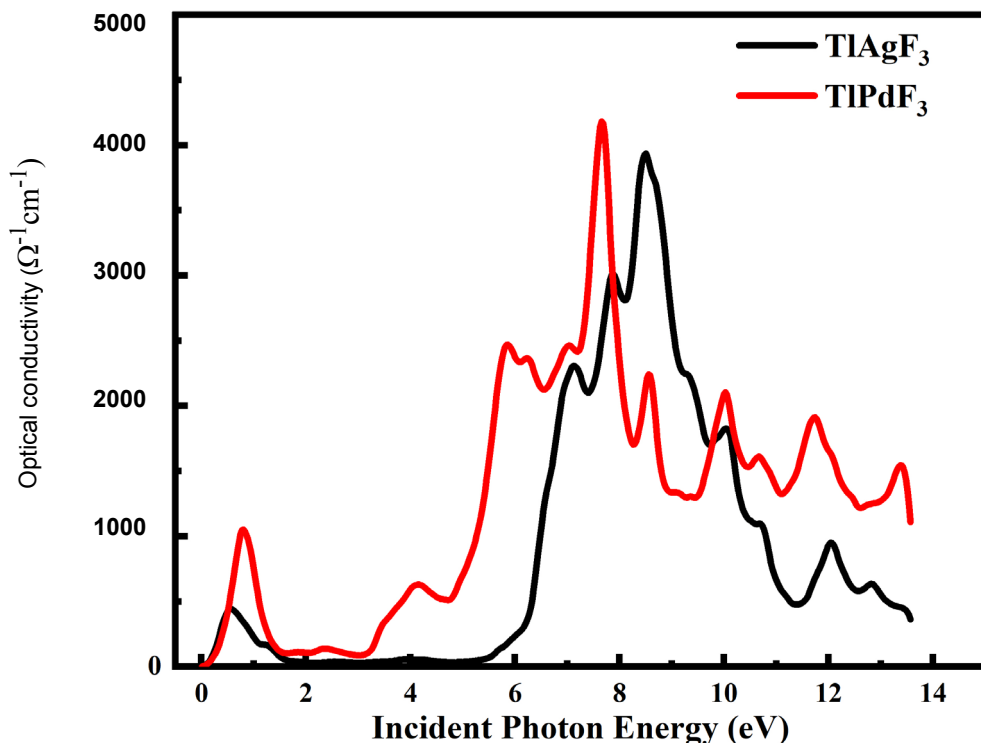


Figure 7. The conductivity $\sigma(\omega)$ of $TlPdF_3$ and $TlAgF_3$.

6.4 THE ABSORPTION $I(\omega)$

Figure 8 shows the analysis of absorption coefficient $I(\omega)$ for both $TlPdF_3$ and $TlAgF_3$ compounds. Both compounds show proper absorption on incident radiation and then it starts absorbing electromagnetic radiation at certain point called threshold point [17]. Threshold points for $TlPdF_3$ is to be 1.6eV while for and $TlAgF_3$ it is 2.3eV respectively. In our case the maximum absorption is at 7.5eV and 8.9eV for $TlPdF_3$ and $TlAgF_3$ respectively.

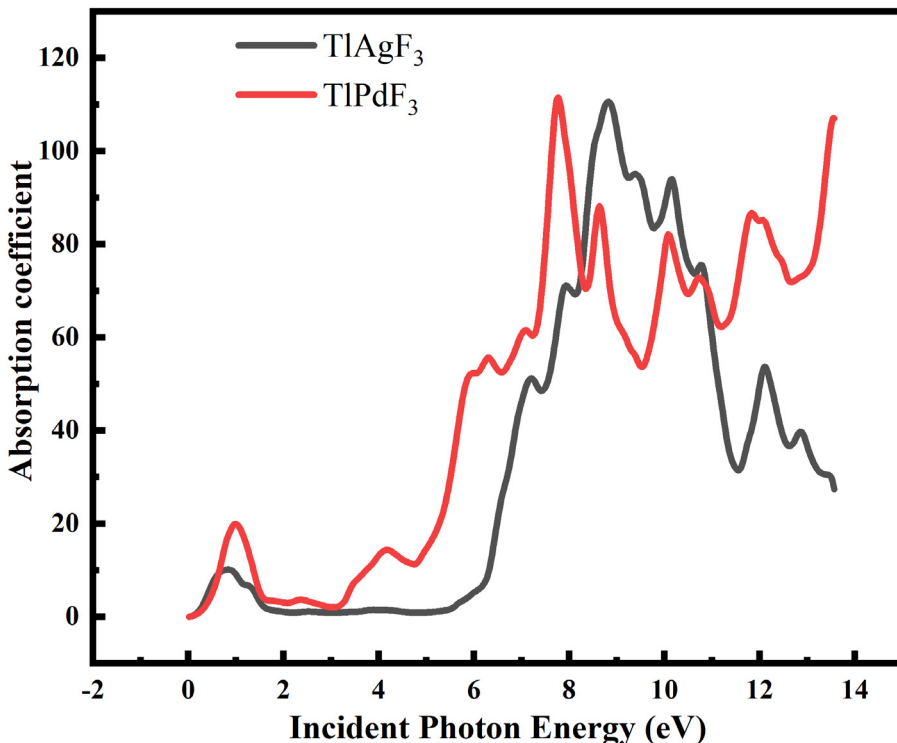


Figure 8. The calculated absorption coefficient $I(\omega)$ of $TlPdF_3$ and $TlAgF_3$.

7. ELASTIC PROPERTIES

For simple cubic structure C_{ij} (where $i = 1, 1, 4$ and $j = 1, 2, 4$) are three independent elastic constants. The FP-LAPW scheme is used in wien2k package. The cubic unit cell is deformed to find out these constants using proper strain tensor to yield an energy–strain relation [18].

The elastic constants C_{ij} are calculated for the compounds $TlPdF_3$ and $TlAgF_3$. The computed elastic constants are summarized in Table 2. Mechanical properties can be analyzed by using these elastic constant C_{ij} . Bulk modulus ‘B’ are positive and therefore these constants are positive [19]. Elastic constants C_{ij} constant of solids provide information that how deformation produced and then retrieve to restore their position after the removal of stress. Certain information like an-isotropic behavior and the bonding character can be find out by C_{ij} . Charpin used WIEN2K package to find out these elastic parameters [20]. The calculated bulk modulus and elastic constants from the theoretical elastic constants are shown in Table 2.

$(C_{11}-C_{12})$ is greater than 0, $(C_{11}+2C_{121})$ is greater than 0 and C_{44} is also greater than 0. The mechanical stability in a cubic crystal is described by B: $C_{12} < B < C_{11}$.

The elastic parameters like A, G, E and ν are used in the following relations[20].

$$A = 2C_{44} / C_{11} - C_{12} \quad (ii)$$

$$E = 9GB / 3B+G \quad (iii)$$

$$\nu = 3B - 2G / 2(2B + G) \quad (iv)$$

$$G = \frac{1}{2}(G_V + G_R)$$

$$G_V = \frac{1}{2}(C_{11} - C_{12} + 3C_{44}) \quad (v)$$

$$G_R = 5C_{44}(C_{11}-C_{12}) / 4C_{44}+3(C_{11}-C_{12}) \quad (vi)$$

Table. 2 The obtained Cij and other mechanical parameters

Compound	C ₁₁	C ₁₂	C ₄₄	B	A	G	E	ν	B/G
TiPdF ₃	220.50	76.00	28.03	110	0.388	90.5	212	0.24	1.22
TiAgF ₃	176.0	50.7	20.5	74	0.31	74	296	0.20	1.00

“G” represents shear modulus, “G_V” gives Voigt’s shear modulus with the upper limit of “G” values, “G_R” shows Reuss’s shear modulus with subscript “G” values [21]. A is nearly equals to one for an-isotropic compounds, while deviation from A shows an-isotropy. The rate of anisotropy measures the value of variation from one. In our calculation, the rate of an-isotropy factor is 0.388 and 0.31 for TiPdF₃ and for TiAgF₃ respectively. Hence both materials are an-isotropic. Both materials are highly strong as E values for are very high. E values shows stiffness of the materiel, as it is a fine marking regarding the strength of the material. ν is the Poisson’s ratio, which is very low for covalent materials, i.e, less than 0.1 and nearly equal to 0.25 for ionic compounds. In our case, ν is 0.24 for TiPdF₃ and 0.20 for TiAgF₃. Therefore TiPdF₃ and for TiAgF₃ are ionic in nature and should be assume an intrabonding.

Both these compounds didn't satisfy Pugh’s criteria as indicated by the B/G relation. This relation shows the mechanical properties of material like brittleness and ductility [22]. TiPdF₃ and TiAgF₃ are brittle as both compounds didn't satisfy Pugh’s criteria. If B/G > 1.75, then the material is said to be ductile and this value is the standard for material ductility. In our study, the B/G ratio for TiPdF₃ is 1.22 and 1.00 for TiAgF₃, and hence our compounds are brittle.

CONCLUSIONS

Herein, we investigated the electronic, structural, elastic and optical properties of fluoro-perovskites TiAgF₃ and TiPdF₃ using full potential linearized augmented plane wave method under generalized gradient approximations within Wien2k. From the volume optimization, the optimized lattice constants, bulk modulus (B), and its pressure derivatives of both cubic fluoro-perovskites are investigated. The total DOS plot of TiAgF₃ and TiPdF₃ are examined. In TiPdF₃ compound, the maxima in peaks

364 Research report First principle study of Structural, Electronic, Elastic and Optical properties 364
Fluoride 56(4 Pt 1):351-365 of $TiXF_3$ (X = Ag and Pd) employing accurate Tb-Mbj approach
October-December 2023 Tahir, Husain, Rahman, Sohail, Khan, Neffati, Murtaza, Khan, Iqbal, Ullah,

in the valence region are due to only F atom. This is also evident from the partial DOS plots of Ti, Pd, Ag, and F atoms respectively. We have found from our study that the band gap of $TiAgF_3$ and $TiPdF_3$ overlaps and hence $TiAgF_3$ and $TiPdF_3$ are metallic in nature. Measured the elastic constants (C_{ij}) and elastic module. It is investigated from the elastic properties computation that both compounds are highly stable and hard. Some optical properties like absorption, dielectric function and refractive index are calculated. Static dielectric constant ϵ_1 (o) are approximately 2.24 and the static refractive index η (o) is nearly 1.5.

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- 365 Research report First principle study of Structural, Electronic, Elastic and Optical properties of TlXF₃ (X = Ag and Pd) employing accurate Tb-Mbj approach of TlXF₃ (X = Ag and Pd) employing accurate Tb-Mbj approach 365
Fluoride 56(4 Pt 1):351-365 of TlXF₃ (X = Ag and Pd) employing accurate Tb-Mbj approach
October-December 2023 Tahir, Husain, Rahman, Sohail, Khan, Neffati, Murtaza, Khan, Iqbal, Ullah,
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